

Title (en)

SILICON ON INSULATOR LOGIC CIRCUIT UTILIZING DIODE SWITCHING ELEMENTS

Title (de)

DIODENSCHALTELEMENTE VERWENDENDER SILIZIUM-AUF-ISOLATOR LOGIKSCHALTKREIS

Title (fr)

CIRCUIT LOGIQUE A SILICIUM SUR ISOLANT UTILISANT DES ELEMENTS DE COMMUTATION A DIODE

Publication

EP 1303881 A1 20030423 (EN)

Application

EP 01923119 A 20010403

Priority

- US 0110921 W 20010403
- US 20915100 P 20000602
- US 59111700 A 20000609

Abstract (en)

[origin: WO0197289A1] A logic circuit is formed on a silicon on insulator (SOI) substrate in the thin silicon layer above the insulating buried oxide layer. The logic circuit both SOI field effect transistors (FETs) and SOI diodes to provide for reduced size of the logic circuit and reduced power consumption when the logic circuit is in operation. A method of performing certain logic function is also provided.

IPC 1-7

H01L 27/12; H03K 19/08; H03K 19/096; H03K 19/12

IPC 8 full level

H01L 21/84 (2006.01); **H01L 27/12** (2006.01); **H03K 19/096** (2006.01); **H03K 19/12** (2006.01)

CPC (source: EP)

H01L 21/84 (2013.01); **H01L 27/1203** (2013.01); **H03K 19/0963** (2013.01); **H03K 19/12** (2013.01)

Citation (search report)

See references of WO 0197289A1

Designated contracting state (EPC)

DE FR GB NL

DOCDB simple family (publication)

WO 0197289 A1 20011220; AU 4984201 A 20011224; EP 1303881 A1 20030423; TW 515095 B 20021221

DOCDB simple family (application)

US 0110921 W 20010403; AU 4984201 A 20010403; EP 01923119 A 20010403; TW 90113314 A 20010601